

ABSTRACT OF THE DISCLOSURE

A method for processing a partially fabricated semiconductor wafer having a layer of nichrome resistor material patterned to form a plurality of nichrome resistors on a surface of the wafer includes performing a wet pre-metallization cleaning step on the wafer surface, performing
5 an RF argon plasma sputter etching process on the wafer surface, advancing the wafer into a second reactor without breaking a vacuum in either reactor, depositing a layer of metal on the surface, patterning the metal to form a predetermined metal interconnection pattern thereof, performing a stabilization bake cycles on the wafer, measuring the TCR of the nichrome resistor material, and rejecting the wafer if the measured TCR is greater than a predetermined value.